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- Inverest in East Serman semi-conductor research and development, and in particular in the development of transistors, on the part of the USOR and the satellite countries; has been great. The Soviets initiated transistor acvelopment at VEB Werk fuer Fernmeldewesen (formerly OSW), in Borlin-Oberachoeneweide, and they also kept themselves informed on the progress of transistor development et VEB Werk fuer Bauelemente der Nechrichtersechnik, Carl von Casietzky (formerly Dralowid) in Teltowid 25X1
- In April 1953, the East German government issued an order (Regierungsboschluas U215D/IV) concerning the cooperation of East Germany with the setablite countries in the field of the development of semi-conductors. Tepartment for Scientific-Technical Cooperation), of the State Flamming Commission, Assued instructions for carrying our this order. According to the terms of these instructions, two Hungarian delegates Acre authorized to visit the Iralowid plant, the Academy Institute for Reasurch on the Physics of Bolkds, and the OST plant, in order to obtain information on the development of transisters, the methods of purification of gormanium, and on the development of thermistors. It was furthermore stipulated that copies of the documentary material pertaining to the development of transistors and therm stors was to be made available to the Hungarian delegates of they desired it. The management of the Dralowid plant in particular was ordered to comply with any demand of the Hungarian ielegates. For unknown reasons, however, hangary had failed to send the lelerates to fast Germany as of November 1938. their visit was deferred but our cancerred.
- 3. In Deptember 1954, beven Geechoslovak t-caracters visited East Germany water the auspices of MIZ and made extended studies on the development of of germanium and silicon drodes and of transistors in the Dralowid and OSW plints, the Academy Institute for Research on the Physics of Solids in Berlin-Buch, and in the Academy Institute for Oscillation Research (Rein-rich Hertz-Enstitut) in Berlin Adlershor2. In October 1954, a Czech semiconductor specialist, Matthias (fnu), arraved for a four-week visit in East Germany and made studies on the Dralowid and CST plants and the Academy Institute for Research on the Physics of Solida in Berlin-Buch This visit was also organized by WTZ. 25X1

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Nuch, for a prolonged stronsistor research. E	dis visit too, was a	sponsored by TZ.	
Comment: This coveragement. It is, he generally and on german interested in the use of aigh-frequency technologisdes procured from the	nium in particular, of germanium and sil ogy. The Institute	t research on semi The Czech visite Licon diodes for y	-conductors ors were mostly ourposes of
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